Corrigendum

Corrigendum to “(Photo)electrochemical Methods for the Determination of the Band Edge Positions of TiO_2 -Based Nanomaterials”

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The paper titled “(Photo)electrochemical Methods for the Determination of the Band Edge Positions of TiO_2 -Based Nanomaterials” [1] contains an error in Figure 3(b) where the work function of the semiconductor, Φ_s , should be depicted as the energy difference between the semiconductor Fermi level and the local vacuum level just outside the semiconductor surface. The corrected Figure 3 is shown as follows.

References

- [1] R. Beranek, “(Photo)electrochemical methods for the determination of the band edge positions of TiO_2 -based nanomaterials,” *Advances in Physical Chemistry*, vol. 2011, Article ID 786759, 20 pages, 2011.

FIGURE 3: Schematic energy model of the n-type semiconductor/electrolyte interface before (a) and after (b) the establishment of equilibrium. The presence of surface states in the semiconductor is neglected. D_{red} and D_{ox} correspond to the distribution functions of the density of states for reduced and oxidized species, respectively, of the redox system (the energy distribution of reduced and oxidized species is different due to different solvation; λ is the reorganization energy). Φ , χ , and IE are the work function, electron affinity, and ionization energy, respectively, of the semiconductor (index_S) and of the electrolyte (index_E).